

Supplementary Information

Manipulation of Rashba effect in layered tellurides MTe (M=Ge, Sn, Pb)

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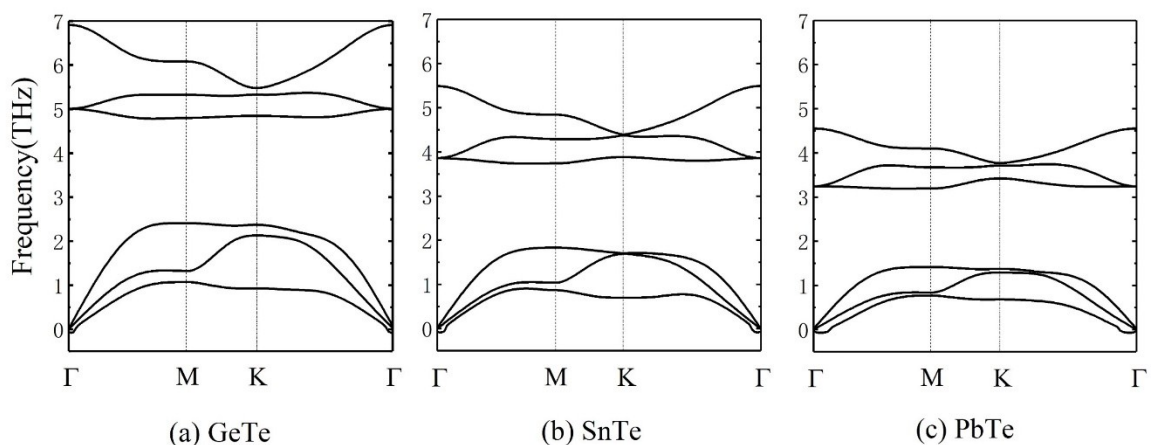


Figure.S1. Phonon spectra of (a) GeTe monolayer, (b) SnTe monolayer and (c) PbTe monolayer.

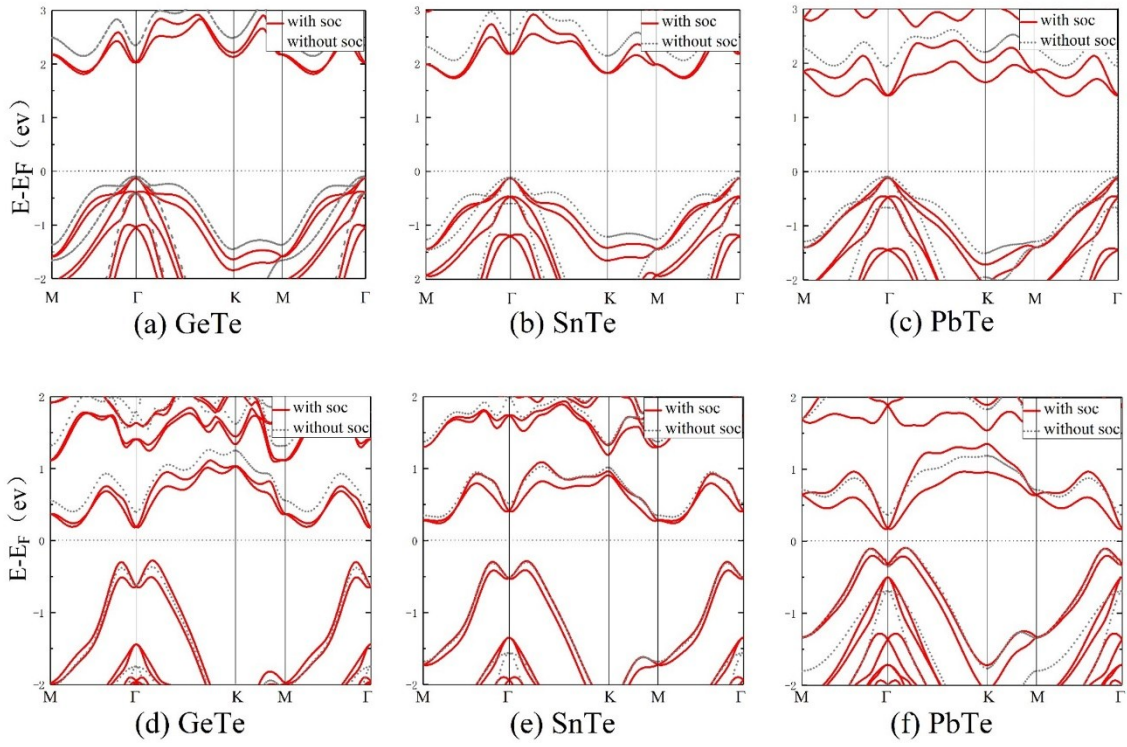


Figure.S2. Band structures of MTe monolayer (a-c) and bilayer (d-f) at the HSE06 level with and without inclusion of SOC.

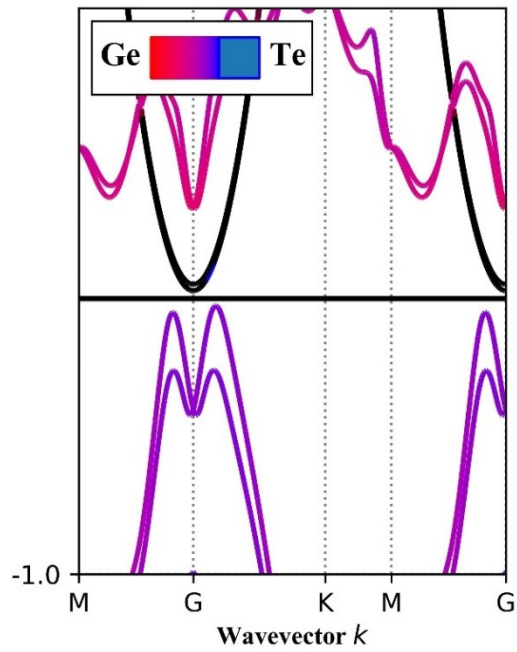


Figure S3. Band structure of bilayer GeTe under a large external electric field of  $0.4\text{V}/\text{\AA}$ .